



## N-Channel Enhancement Mode Field Effect Transistor

### Product Summary

$V_{DS}$  60V

$I_D$  3A

D/F2 1/F2 1Tm0 gTmr9((nn)4ON)000008882 0 596.04 842.04 reW\* n



# YJL03N06AL

## Electrical Characteristics ( $T_J=25$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
<b>Static Parameter</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	60	-	-	



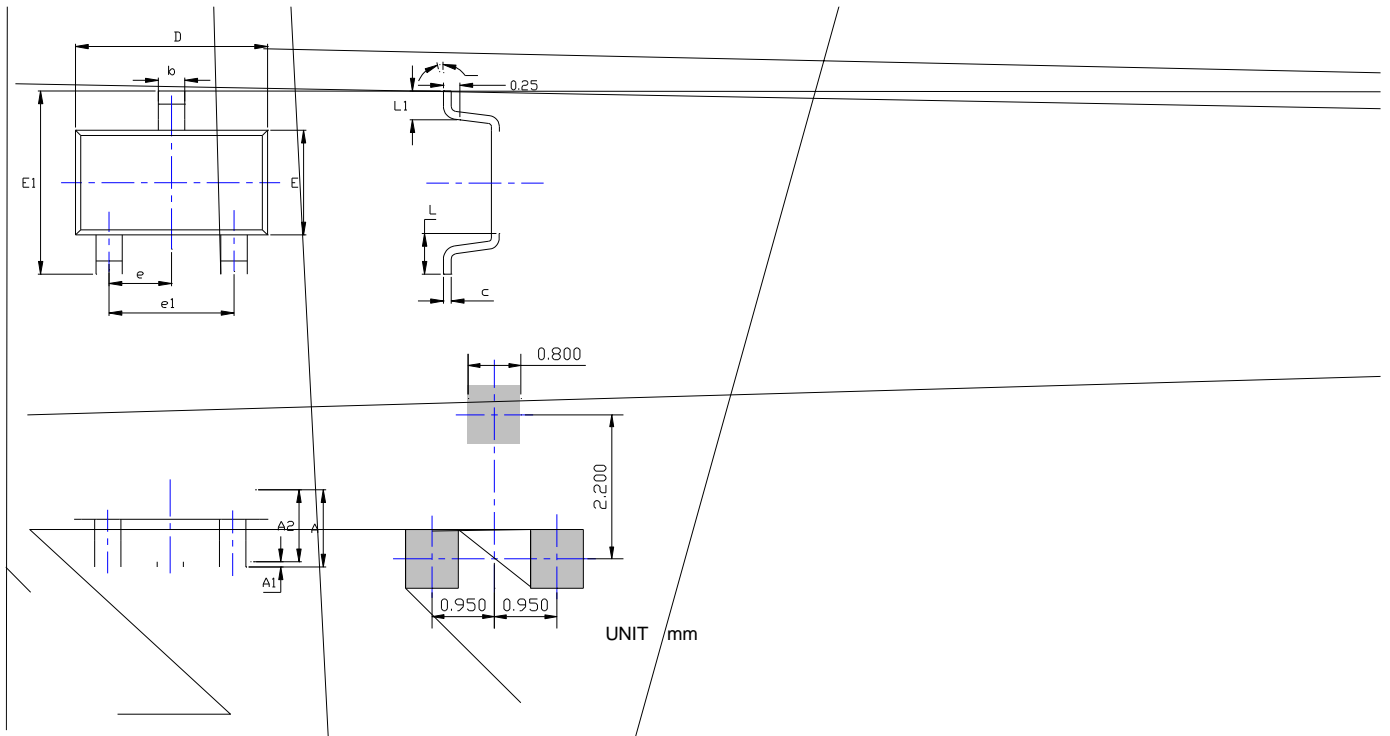








SOT-23-3L Package information





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